

Negative E-Beam Resist Medusa 84 SiH

ALLRESIST



High resolution,
Improved shelf life, Improved stability,
Elimination of the presumably
carcinogenic solvent MIBK,

Storage: -18-10°C

Highest resolution of 6 nm lines

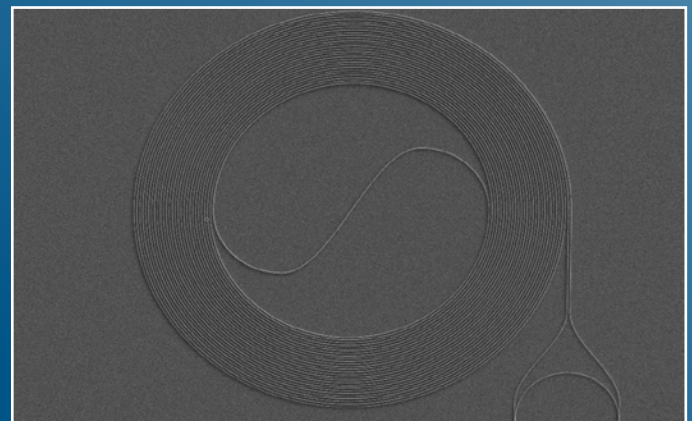
Dose to clear: approx. 230 $\mu\text{C}/\text{cm}^2$ @30kV

Resist thickness: up to 800 nm



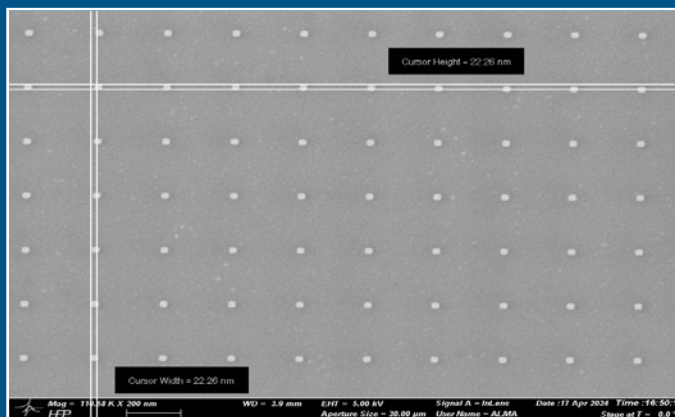
Single line structures of Medusa 84 SiH on GaAs,
written at 30 kV.

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100 nm line/space structures written on silicon at
 $1000 \mu\text{C}/\text{cm}^2$ at 100 kV.

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Square pillars with a diameter of 22 nm and a height
of 50 nm height on GaAs.

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Nanorods with a spacing of $1 \mu\text{m}$ written on
silicon at $2000 \mu\text{C}/\text{cm}^2$ at 50kV.

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